US 20090020156A1

(19) United States

(12) Patent Application Publication

(10) Pub. No.: US 2009/0020156 A1

(43) Pub. Date: Jan. 22, 2009

Ohtsuka et al.

(54) METHOD FOR MANUFACTURING SOLAR CELL AND SOLAR CELL

(75) Inventors: **Hiroyuki Ohtsuka**, Gunma (JP); **Naoki Ishikawa**, Gunma (JP); **Masatoshi Takahashi**, Gunma (JP)

Correspondence Address:
OLIFF & BERRIDGE, PLC
P.O. BOX 320850
ALEXANDRIA, VA 22320-4850 (US)

(73) Assignees: **SHIN-ETSU HANDOTAI CO., LTD.**, TOKYO (JP); **SHIN-ETSU CHEMICAL CO., LTD.**, TOKYO (JP)

(21) Appl. No.: **11/918,899**

(22) PCT Filed: **Apr. 7, 2006**

(86) PCT No.: **PCT/JP2006/307429**

§ 371 (c)(1),
(2), (4) Date: **Oct. 19, 2007**

(30) **Foreign Application Priority Data**

Apr. 26, 2005 (JP) 2005-127898

Publication Classification

(51) **Int. Cl.**

H01L 31/00	(2006.01)
H01L 31/18	(2006.01)
H01L 21/20	(2006.01)
H01L 21/22	(2006.01)

(52) **U.S. Cl.** **136/256**; 438/57; 438/478; 438/542; 257/E21.09; 257/E21.135

(57) **ABSTRACT**

The present invention is a method for manufacturing a solar cell by forming a pn junction in a semiconductor substrate having a first conductivity type to manufacture a solar cell, including at least: applying a first coating material containing a dopant onto the semiconductor substrate having the first conductivity type; and performing vapor-phase diffusion heat treatment to form a first diffusion layer in a region applied with the first coating material and a second diffusion layer, which is formed next to the first diffusion layer through vapor-phase diffusion, with a conductivity lower than a conductivity of the first diffusion layer at the same time, and provides a solar cell. Hence, it is possible to provide a method for manufacturing a solar cell, which can manufacture a solar cell at a low cost in a simple and easy way while suppressing surface recombination in a light-receiving surface other than an electrode region and recombination in an emitter to increase photoelectric conversion efficiency of the solar cell, and a solar cell.